

Mark Lundstrom

List of Publications by Year in descending order

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24
papers

7,792
citations

471061

17
h-index

676716

22
g-index

25
all docs

25
docs citations

25
times ranked

6493
citing authors

#	ARTICLE	IF	CITATIONS
1	Ballistic carbon nanotube field-effect transistors. <i>Nature</i> , 2003, 424, 654-657.	13.7	2,883
2	High- κ dielectrics for advanced carbon-nanotube transistors and logic gates. <i>Nature Materials</i> , 2002, 1, 241-246.	13.3	928
3	High-Field Quasiballistic Transport in Short Carbon Nanotubes. <i>Physical Review Letters</i> , 2004, 92, 106804.	2.9	543
4	Self-Aligned Ballistic Molecular Transistors and Electrically Parallel Nanotube Arrays. <i>Nano Letters</i> , 2004, 4, 1319-1322.	4.5	505
5	Carbon Nanotube Field-Effect Transistors with Integrated Ohmic Contacts and High- κ Gate Dielectrics. <i>Nano Letters</i> , 2004, 4, 447-450.	4.5	498
6	A three-dimensional quantum simulation of silicon nanowire transistors with the effective-mass approximation. <i>Journal of Applied Physics</i> , 2004, 96, 2192-2203.	1.1	328
7	Toward Multiscale Modeling of Carbon Nanotube Transistors. <i>International Journal for Multiscale Computational Engineering</i> , 2004, 2, 257-276.	0.8	224
8	Performance projections for ballistic carbon nanotube field-effect transistors. <i>Applied Physics Letters</i> , 2002, 80, 3192-3194.	1.5	200
9	Performance Analysis of a Ge/Si Core/Shell Nanowire Field-Effect Transistor. <i>Nano Letters</i> , 2007, 7, 642-646.	4.5	157
10	Theoretical investigation of surface roughness scattering in silicon nanowire transistors. <i>Applied Physics Letters</i> , 2005, 87, 043101.	1.5	134
11	Metal-insulator-semiconductor electrostatics of carbon nanotubes. <i>Applied Physics Letters</i> , 2002, 81, 1486-1488.	1.5	114
12	Role of phonon scattering in carbon nanotube field-effect transistors. <i>Applied Physics Letters</i> , 2005, 86, 193103.	1.5	93
13	Ultimate device scaling: Intrinsic performance comparisons of carbon-based, InGaAs, and Si field-effect transistors for 5 nm gate length. , 2011, , .		65
14	Performance evaluation of ballistic silicon nanowire transistors with atomic-basis dispersion relations. <i>Applied Physics Letters</i> , 2005, 86, 093113.	1.5	47
15	Minority electron transport in InP/InGaAs heterojunction bipolar transistors. <i>Applied Physics Letters</i> , 1992, 61, 465-467.	1.5	32
16	CARBON NANOTUBE FIELD-EFFECT TRANSISTORS. <i>International Journal of High Speed Electronics and Systems</i> , 2006, 16, 897-912.	0.3	32
17	Signatures of Disorder in the Minimum Conductivity of Graphene. <i>Nano Letters</i> , 2011, 11, 1319-1322.	4.5	27
18	Atomistic Simulation of Carbon Nanotube Field-Effect Transistors Using Non-Equilibrium Green's Function Formalism. <i>Journal of Computational Electronics</i> , 2004, 3, 373-377.	1.3	24

#	ARTICLE	IF	CITATIONS
19	Device Simulation of SWNT-FETs. Integrated Circuits and Systems, 2009, , 107-131.	0.2	14
20	Consequences of valley filtering on abrupt junction AlGaAs/GaAs heterojunction bipolar transistors. Journal of Applied Physics, 1989, 66, 2168-2172.	1.1	6
21	3D Electrostatics of Carbon Nanotube Field-Effect Transistors. Journal of Computational Electronics, 2004, 3, 277-280.	1.3	4
22	A Quantum Mechanical Approach for the Simulation of Si/SiO ₂ Interface Roughness Scattering in Silicon Nanowire Transistors. Journal of Computational Electronics, 2004, 3, 453-457.	1.3	4
23	Investigative Tools: Theory, Modeling, and Simulation. , 2011, , 29-69.		4
24	CARBON NANOTUBE FIELD-EFFECT TRANSISTORS. Selected Topics in Electornics and Systems, 2007, , 15-30.	0.2	1